











absorption and emission cross-sections present in  $\text{Yb}^{3+}$ -doped double tungstates, make it an attractive high-gain laser device.

In the future, replacing the butt-coupled mirrors with an on-chip integrated cavity by etching Bragg reflectors or a distributed-feedback grating into the channel waveguide [1] or employing a ring-resonator configuration will make the device more robust and environmentally stable, such that real-world applications can seriously be envisaged.

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